To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HSM126S

Silicon Schottky Barrier Diode for System Protection

ADE-208-111C (Z)

Rev. 3
May 1995

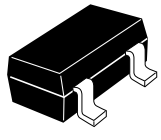
Features

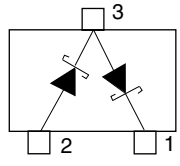
- HSM126S which is connected in series configuration enable to protect electric systems from miss-operation against external + and – surge.
- Low V_F and low leakage current.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM126S	S14	MPAK

Pin Arrangement





(Top View)

1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

Absolute Maximum Ratings*[3]

(Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	I_O*[1]	200	mA
Non-Repetitive peak forward surge current	I_{FSM}*[2]	2	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Notes: 1. Sine wave, Two device total
2. 50Hz half sine wave 1 pulse
3. Per one device

Electrical Characteristics*

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	2.0	µA	V_R = 5V
Forward voltage	V_F	—	—	0.35	V	I_F = 10mA
Capacitance	C	—	40	—	pF	V_R = 0V, f = 1MHz

Note: Per one device

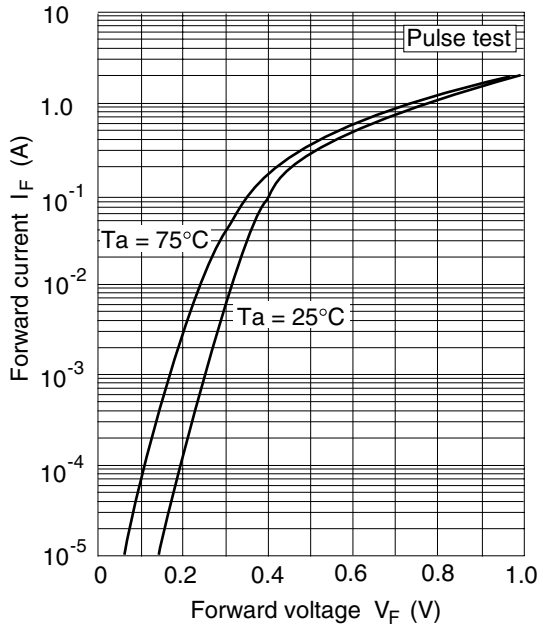


Fig.1 Forward current Vs. Forward voltage

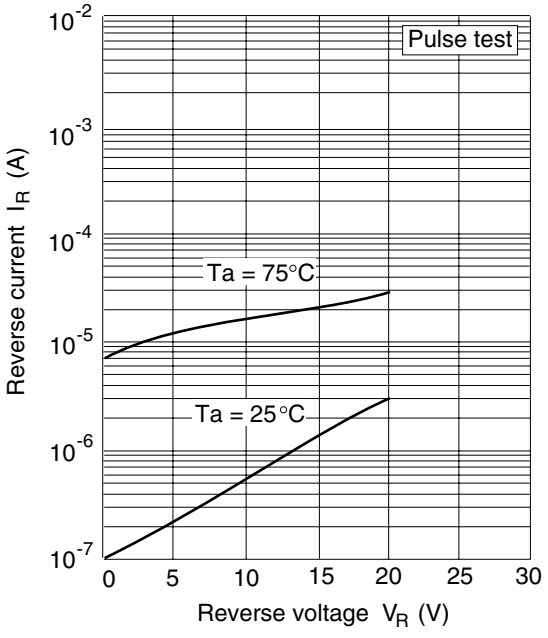


Fig.2 Reverse current Vs. Reverse voltage

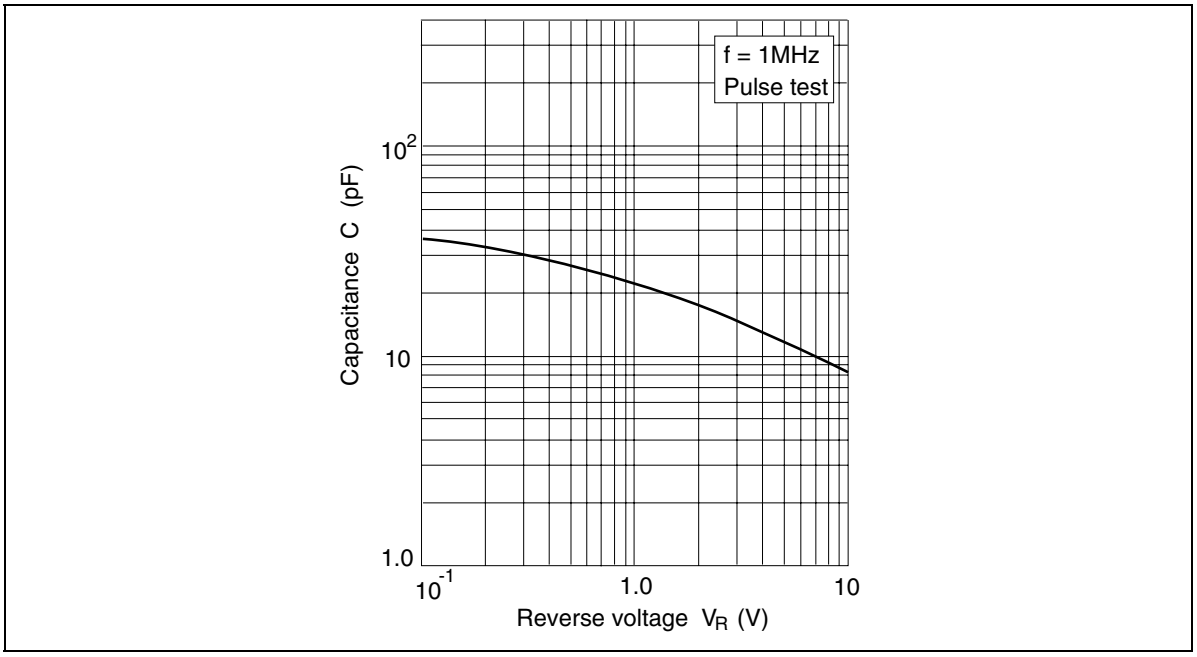
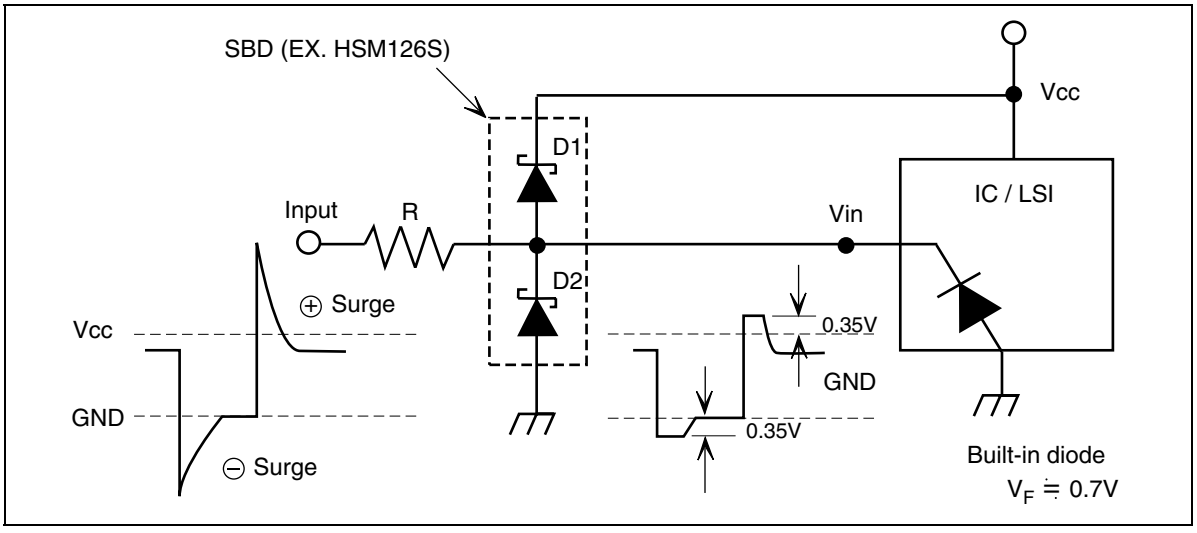


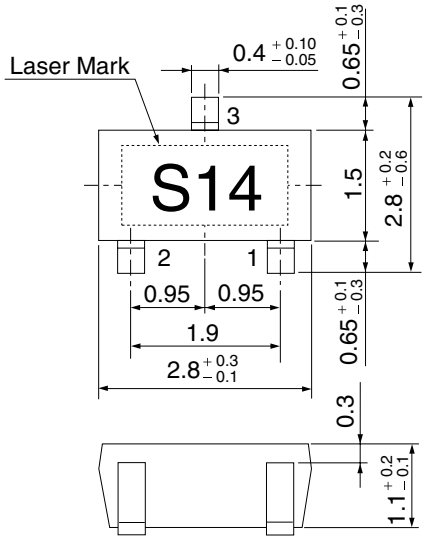
Fig.3 Capacitance Vs. Reverse voltage

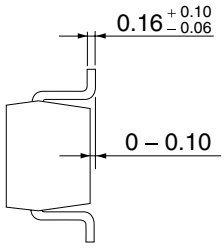
Example of application circuite



Package Dimensions

Unit: mm





1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011

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